

EMIPAK 1B PressFit Power Module 650 V HF Output Rectification, Flexible Configuration, 20 A



EMIPAK 1B (package example)

PRIMARY CHARACTERISTICS					
D1 - D12					
V_{RRM}	650 V				
V _{FM} typical at 20 A	1.70 V				
I _O at T _{SINK} = 99 °C	20 A				
t _{rr} typical at 20 A	65 ns				
Package	EMIPAK 1B				
Circuit configuration	6 x independent ultrafast rectifiers legs for output rectification				
Туре	Modules - diode, FRED Pt®				

FEATURES

- FRED Pt® diode technology
- Exposed Al₂O₃ substrate with low thermal resistance



- Ultra soft reverse recovery
- · Low internal inductances
- Qualified using AQG324 guideline as reference
- PressFit pins locking technology PATENT(S): www.vishav.com/patents
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION

The EMIPAK 1B package is easy to use thanks to the PressFit pins. The exposed substrate provides improved thermal performance.

The optimized layout also helps to minimize stray parameters, allowing for better EMI performance.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Operating junction temperature	TJ		175	°C
Storage temperature range	T _{Stg}		-40 to +150	C
RMS isolation voltage	V _{ISOL}	$T_J = 25$ °C, all terminals shorted, $f = 50$ Hz, $t = 1$ s	3500	V
D1 - D12				
Maximum average forward current (per diode)	1	T _{SINK} = 25 °C	31	Α
Maximum average forward current (per diode)	I _{F(AV)}	T _{SINK} = 80 °C	23	A
Dower dissipation	В	T _{SINK} = 25 °C	68	W
Power dissipation	P_D	T _{SINK} = 80 °C	43	VV
Maximum peak one cycle forward non-repetitive		10 ms sine or 6 ms rectangular pulse, $T_J = 25 ^{\circ}\text{C}$, no voltage reapplied	160	Α
surge current	1 Olvi	8.3 ms sine, T _J = 25 °C, no voltage reapplied	167	Α
Maximum I ² t capability for fusing	l ² t	No voltage reapplied, t = 10 ms	128	A ² s
Maximum 1-t capability for fusing	1-1	No voltage reapplied, t = 8.3 ms	117	A-5
Maximum I ² √t capability for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied	1281	A²√s
Repetitive peak reverse voltage	V_{RRM}		650	V
Low level value of threshold voltage	V _{F(TO)1}	$(16.7 \% \text{ x } I_{F(AV)} < I < \text{x } I_{F(AV)}), T_J = T_J \text{ maximum}$	1.03	V
High level value of threshold voltage	V _{F(TO)2}	$(I > x I_{F(AV)}), T_J = T_J \text{ maximum}$ 1.3		V
Low level value of forward slope resistance	r _{f1}	r_{f1} (16.7 % x $I_{F(AV)}$ < I < x $I_{F(AV)}$), $T_J = T_J$ maximum		mΩ
High level value of forward slope resistance	r _{f2}	$(I > x I_{F(AV)}), T_J = T_J maximum$	38.3	11122

PATENT(S): www.vishay.com/patents

This Vishay product is protected by one or more United States and international patents.



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS	
D1 - D12	D1 - D12						
Forward voltage drop	V	I _F = 20 A	-	1.70	2.10	V	
Torward voltage drop	V_{FM}	I _F = 20 A, T _J = 175 °C	-	1.33	-	, v	
Breakdown voltage	V_{BR}	I _R = 100 μA	650	-	-	V	
Reverse leakage current	_	V _R = 650 V	-	0.3	10	μA	
neverse leakage current	IRM	V _R = 650 V, T _J = 175 °C	-	90	-	μΑ	

SWITCHING CHARACTERISTICS (T _J = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
D1 - D12						
Diode reverse recovery time	t _{rr}	V _B = 400 V,	-	65	-	ns
Diode reverse recovery current	I _{rr}	I _F = 20 A,	-	8.5	-	Α
Diode reverse recovery charge	Q_{rr}	dl/dt = 500 A/µs	-	275	-	nC
Diode reverse recovery time	t _{rr}	V _B = 400 V,	-	111	-	ns
Diode reverse recovery current	I _{rr}	I _F = 20 A,	-	14.8	-	Α
Diode reverse recovery charge	Q_{rr}	dl/dt = 500 A/μs, T _J = 125 °C	-	821	-	nC

INTERNAL NTC - THERMISTOR SPECIFICATIONS						
PARAMETER SYMBOL TEST CONDITIONS				UNITS		
Resistance	R ₂₅	T _C = 25 °C	5000	Ω		
Resistance	R ₁₀₀	T _C = 100 °C	493 ± 5 %	52		
B-value	B _{25/50}	$R_2 = R_{25} \text{ exp. } [B_{25/50}(1/T2 - 1/(298.15K))]$	3375 ± 5 %	K		
Maximum operating temperature			220	°C		
Dissipation constant			2	mW/°C		
Thermal time constant			8	s		

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	
D1 - D12 - thermal resistance junction to sink (per diode) (1)	R _{thJS}	-	1.83	-	°C/W	
Case to sink thermal resistance (per module) (1)		-	0.1	-	C/VV	
Mounting torque (M4)		2	-	3	Nm	
Weight		-	28	-	g	

Note

 $^{^{(1)}}$ Mounting surface flat, smooth, and greased, λ_{grease} = 0.67 W/mK



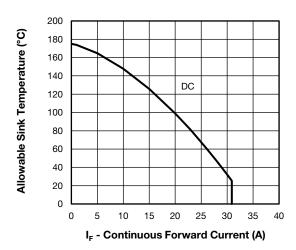


Fig. 1 - Allowable Sink Temperature vs. Continuous Forward Current (Forward Current vs. Sink Temperature)

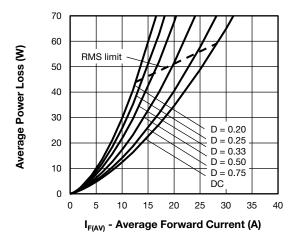


Fig. 2 - Average Power Loss vs. Average Forward Current (Forward Power Loss Characteristics)

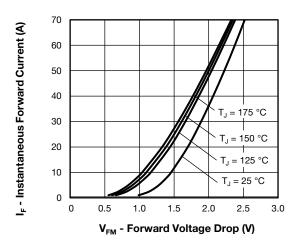


Fig. 3 - Typical Forward Voltage Drop vs. Instantaneous Forward Current (Per Diode)

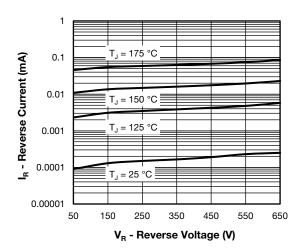


Fig. 4 - Typical Reverse Current vs. Reverse Voltage (Per Diode)

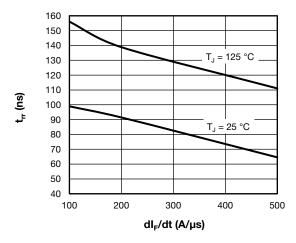


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt (Per Diode) $V_{rr} = 400 \text{ V}, I_F = 20 \text{ A}$

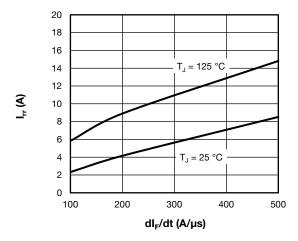


Fig. 6 - Typical Reverse Recovery Current vs. dI_F/dt (Per Diode) $V_{rr} = 400 \text{ V}, I_F = 20 \text{ A}$

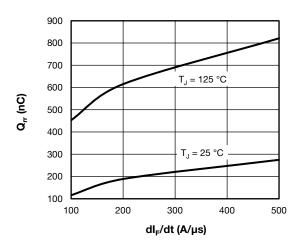
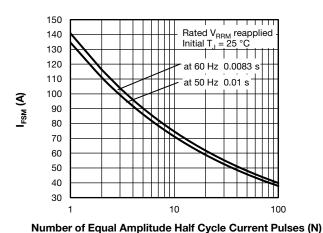
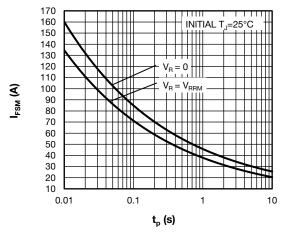


Fig. 7 - Typical Reverse Recovery Charge vs. dI_F/dt (Per Diode) $V_{rr} = 400 \ V, \, I_F = 20 \ A$



 $\label{eq:Fig. 8-IFSM} \mbox{Fig. 8-I}_{\rm FSM} \mbox{ vs. N}$ (Non-Repetitive Peak Forward Surge Current vs. Number Pulses)



 $\label{eq:Fig.9} \textit{Fig. 9} - \textit{I}_{FSM} \, \textit{vs. t}_{p} \\ \textit{(Non-Repetitive Peak Forward Surge Current vs Pulse Duration)}$

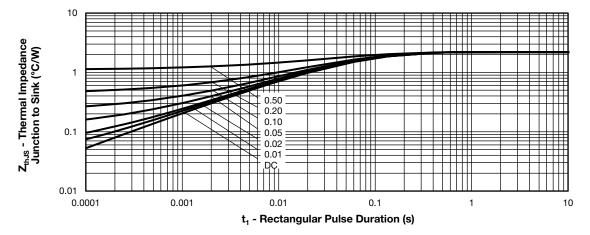


Fig. 10 - Z_{thJS} Thermal Impedance Junction to Sink vs. t1 Rectangular Pulse Duration (Maximum Thermal Impedance Z_{thJS} Characteristics Per Diode)

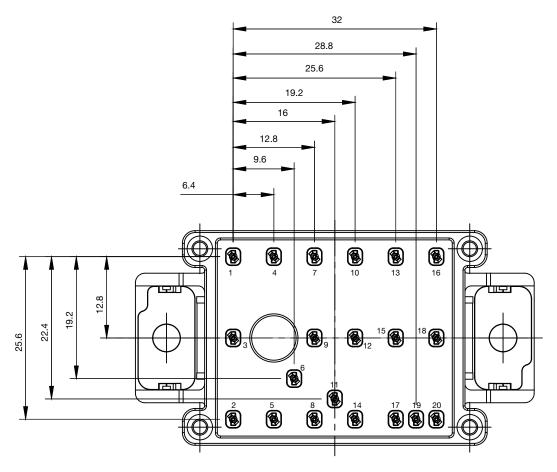


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CIRCUIT CONFIG	CIRCUIT CONFIGURATION							
CIRCUIT	CIRCUIT CONFIGURATION CODE			•	CIRCUIT DI	RAWING		
		1	4	7 0	10	13 Q	16 O	
		D1	D3	D5	D7	D9	D11	
6 x independent ultrafast rectifiers legs for output	V	3 o —	6 🗪	9 🗪	12 🗨	15 🗨	18 🗨	O 19
rectification		D2	D4	D6	D8	D10	D12	Th O 20
		0 2	5	o 8	O	o	O 17	

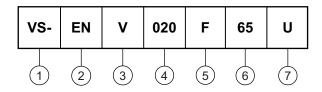
PACKAGE





ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Package indicator (EN = EMIPAK 1B)

Gircuit configuration (V = 6 x independent ultrafast rectifiers legs for output rectification)

4 - Current rating (020 = 20 A)

5 - Switch die technology (F = FRED Pt® diode)

6 - Voltage rating (65 = 650 V)

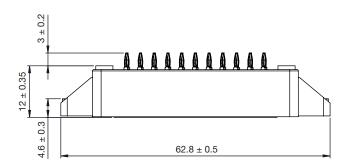
7 - Diode die technology (U = FRED Pt diode with ultra soft reverse recovery)

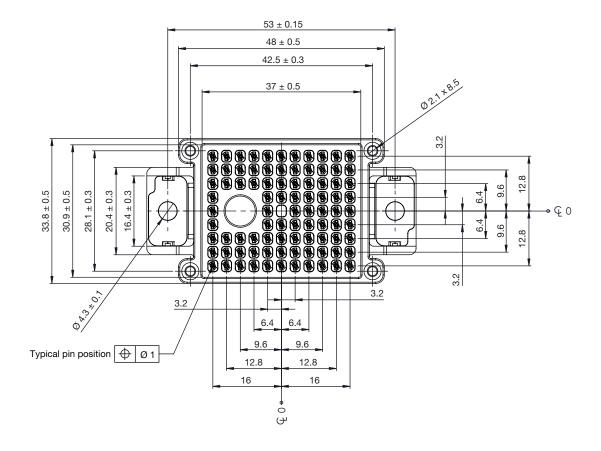
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95558</u>					
Application Note	www.vishay.com/doc?95580				



EMIPAK-1B PressFit

DIMENSIONS in millimeters







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